Innovative Service Around the Globe YAGEO

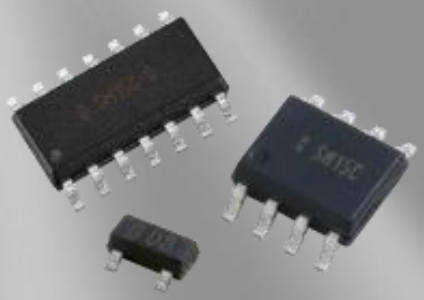
DATA SHEET

ELECTROSTATIC DISCHARGE PROTECTION DEVICES

INDUSTRIAL / CONSUMER

SJD16AXXL01 SERIES

RoHS compliant & Halogen free



Product specification– October 12, 2022 V.4

Electrostatic Discharged Protection Devices (ESD) Data Sheet

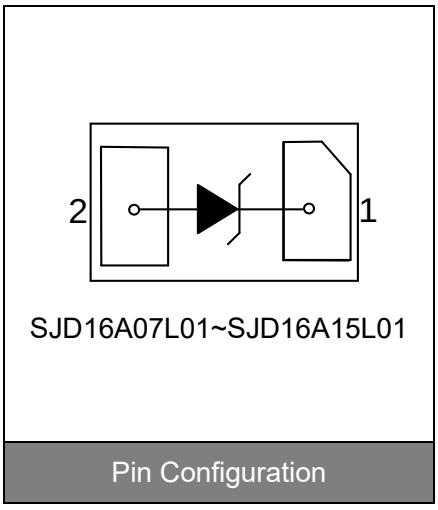
Description

Brightking's SJD16AXXL01 siries are designed to protect power port and the chip Vbus interfaces. It has been specifically designed to protect sensitive components which are connected to power lines from overvoltage caused by electrostatic discharge (ESD),cable discharge events (CDE) and lightning.
These devices integrate a high power transient voltage suppressor(TVS) and small package. It features solid-state silicon-avalanche technology for unmatched transient protection without device degradation. It offers superior electrical characteristics including fast response time, low clamping voltage and no device degradation. This allows the designer maximum flexibility and reduces parts count.
The series devices may be used to meet the immunity requirements of IEC61000-4-2 (ESD), IEC61000-4-4 (EFT) , IEC61000-4-5 (Surge).

Contact : ±30kV
Air : ±30kV

Features

- IEC61000-4-2 ESD 30KV Air, 30KV contact compliance
- DFN1610 surface mount package
- Protects power line
- Working voltage:,7V,10V,12V,15V,
- SJD16A07L01~SJD16A15L01, Cathode rays on the Pin1
- Low leakage current
- Low clamping voltage
- Solid-state silicon avalanche technology
- RoHS compliant
- Solder reflow temperature: Pure Tin-Sn, 260~270℃
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020



SJD16A07L01~SJD16A15L01

Pin Configuration

Applications

- Power port
- I^2C bus protection

Maximum Ratings

Rating	Symbol	Value	Unit
Peak pulse power (tp=10/1000μs waveform)	Ppp	120	W
Peak pulse power(tp=8/20μs waveform) SJD16A07L01~SJD16A15L01	Ppp	2000	W
ESD voltage (Contact discharge)	V_{ESD}	±30	kV
ESD voltage (Air discharge)		±30	
Storage & operating temperature range	T_{STG} ,T_J	-55~+150	℃

Electrical Characteristics (T_J=25℃)

SJD16A07L01(Marking: J07)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				7	V
Reverse breakdown voltage	V_{BR}	I_{BR}=1.0mA	7.3			V
Reverse leakage current	I_R	V_R=7.0V			1.0	μA
Clamping voltage (tp=8/20μs)	V_C	I_{PP}=80A		30		V
Peak Pulse Current(tp=8/20μs)	I_{PP}				80	A
Off state junction capacitance	C_J	0Vdc,f=1MHz Between I/O pins and GND		650		pF

Electrical Characteristics (T_J=25℃)

SJD16A10L01(Marking: J10)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				10	V
Reverse breakdown voltage	V_{BR}	I_{BR}=1.0mA	11			V
Reverse leakage current	I_R	V_R=10V			1.0	μA
Clamping voltage (tp=8/20μs)	V_C	I_{PP}=60A		35		V
Peak Pulse Current(tp=8/20μs)	I_{PP}				60	A
Off state junction capacitance	C_J	0Vdc,f=1MHz Between I/O pins and GND		400		pF

SJD16A12L01 (Marking: J12)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				12	V
Reverse breakdown voltage	V_{BR}	I_{BR}=1.0mA	13			V
Reverse leakage current	I_R	V_R=12V			1.0	μA
Clamping voltage (tp=8/20μs)	V_C	I_{PP}=47A		43		V
Peak Pulse Current(tp=8/20μs)	I_{PP}				47	A
Off state junction capacitance	C_J	0Vdc,f=1MHz Between I/O pins and GND		365		pF

SJD16A15L01(Marking: J15)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				15	V
Reverse breakdown voltage	V_{BR}	I_{BR}=1.0mA	16			V
Reverse leakage current	I_R	V_R=15V			1.0	μA
Clamping voltage (tp=8/20μs)	V_C	I_{PP}=45A		45		V
Peak Pulse Current(tp=8/20μs)	I_{PP}				45	A
Off state junction capacitance	C_J	0Vdc,f=1MHz Between I/O pins and GND		300		pF

Typical Characteristics Curves

Figure 1. Power Derating Curve

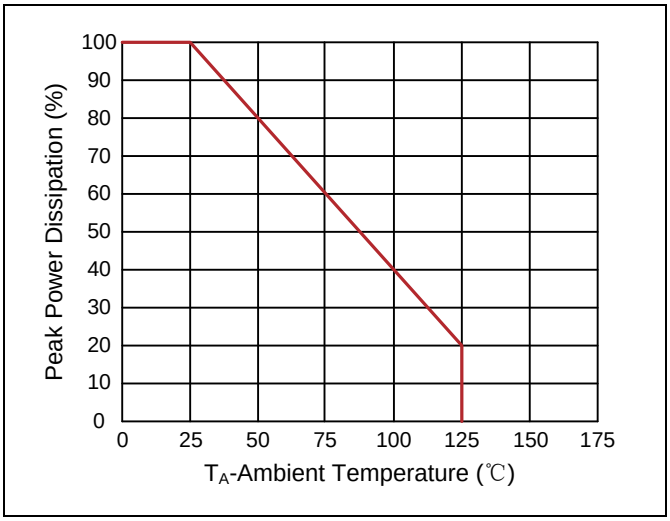


Figure 2. 8/20μs Pulse Waveforms

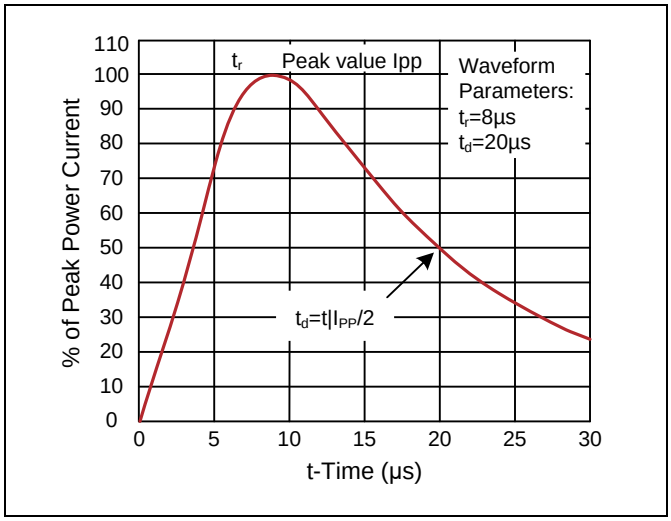


Figure 3. Clamping Voltage vs. Peak Pulse Current

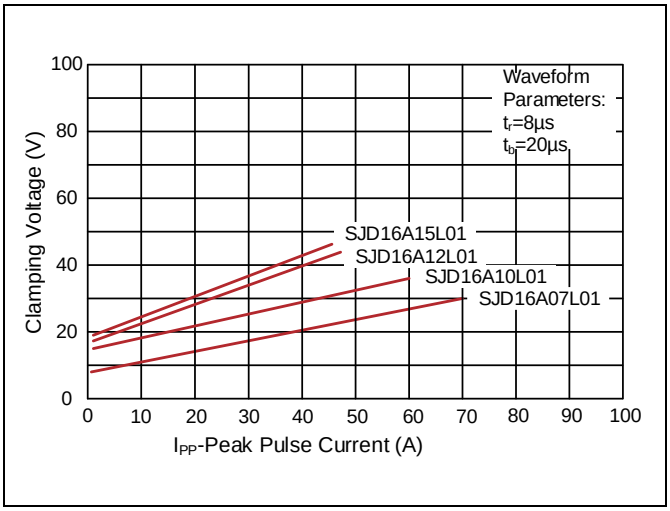


Figure 4. ESD Clamping (8kV Contact IEC61000-4-2)

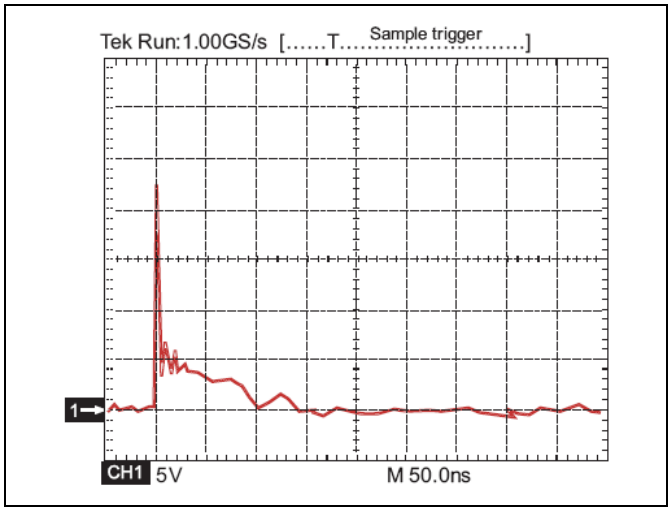


Figure 5. 10/1000μs Pulse Waveform

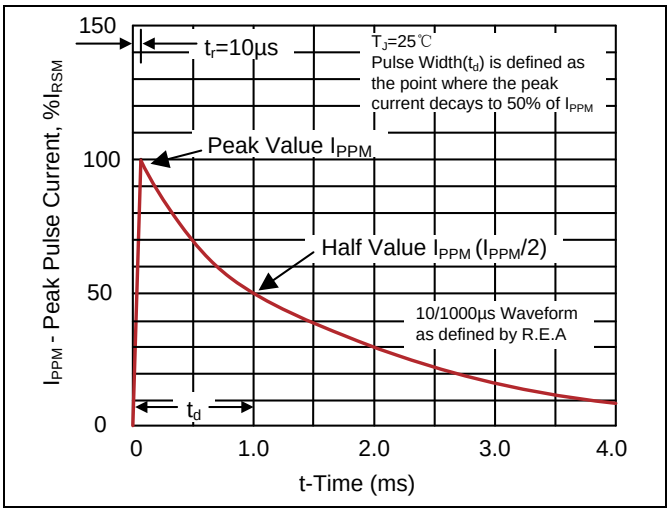
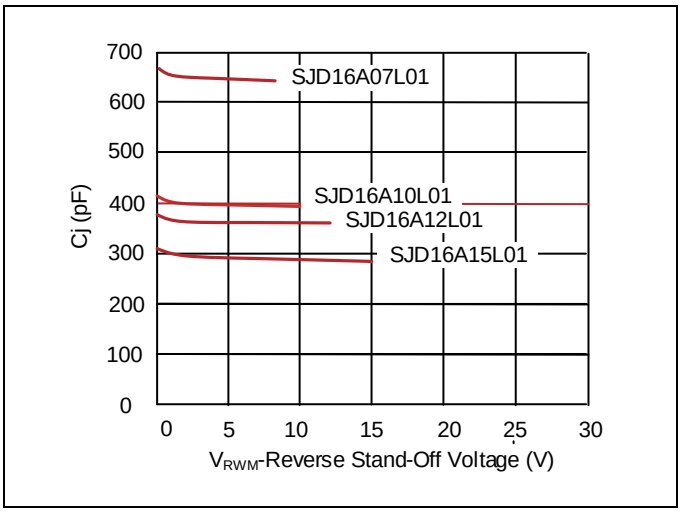
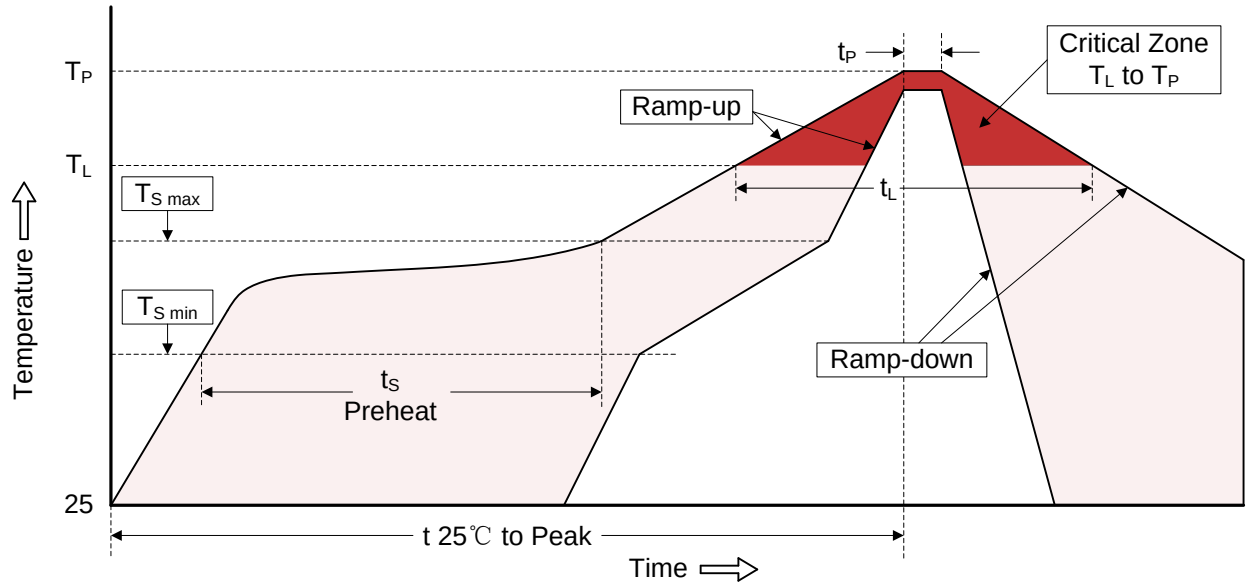


Figure 6. Typical Junction Capacitance



Recommended Soldering Conditions

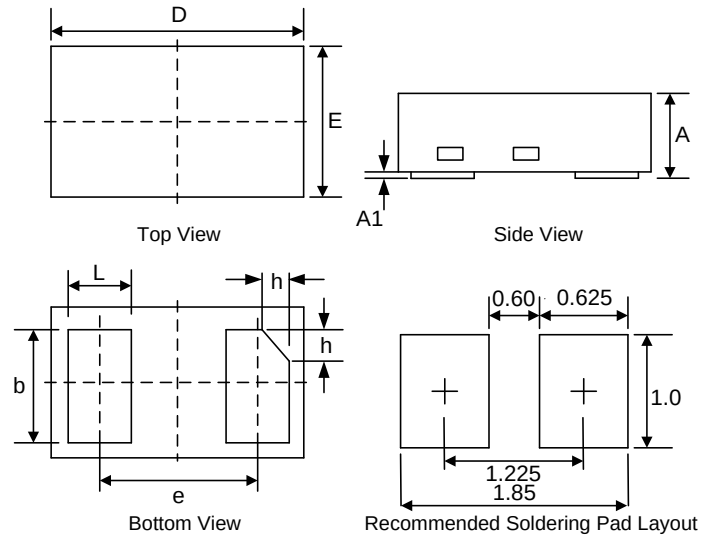
Reflow Soldering



Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (TL to TP)	3℃/second max.
Preheat -Temperature Min (TS min) -Temperature Max (TS max) -Time (min to max) (ts)	150℃ 200℃ 60-180 seconds
TS max to TL -Ramp-up Rate	3℃/second max.
Time maintained above: -Temperature (TL) -Time (tL)	217℃ 60-150 seconds
Peak Temperature (TP)	260℃
Time within 5℃ of actual Peak Temperature (tP)	20-40 seconds
Ramp-down Rate	6℃/second max.
Time 25℃ to Peak Temperature	8 minutes max.

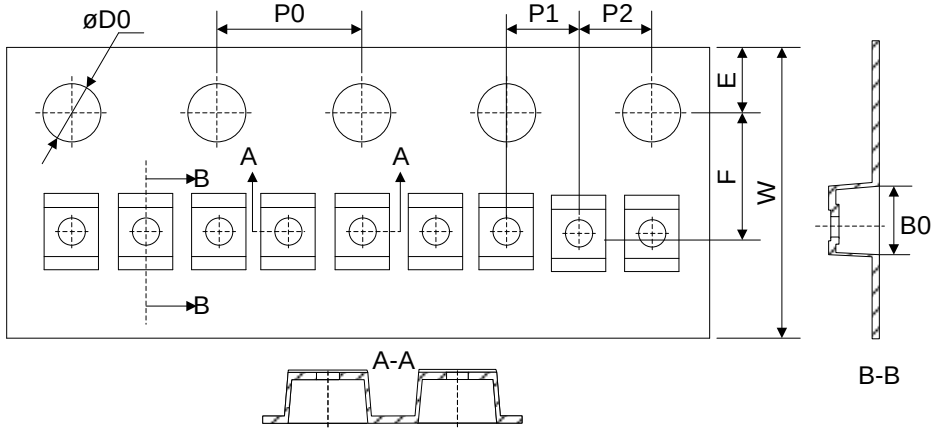
Dimensions (DFN1610)



Symbol	Dimension			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.55	0.66	0.022	0.026
A1	0.00	0.05	0.000	0.002
D	1.55	1.68	0.061	0.066
E	0.95	1.08	0.037	0.043
b	0.8 TYP		0.031 TYP	
e	1.1 TYP		0.043 TYP	
L	0.35	0.45	0.014	0.018
h	0.15	0.25	0.006	0.010

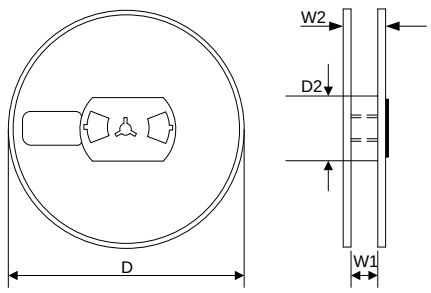
Packaging

Tape



Symbol	Dimension (mm)
W	8.00±0.30
P0	4.00±0.10
P1	2.00±0.10
P2	2.00±0.10
D0	Φ1.50±0.10
E	1.75±0.05
F	3.50±0.10
B0	1.72±0.05

Reel



D	Φ178.0±2.0
D2	Φ54.50±1.0
W1	9.5±2.0
W2	12.30±1.5
Quantity: 5000PCS	